

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of



Confirmation No. 8985

SOTOME, Yoshihiro

Allowed: February 18, 2004

Serial No. 10/038,680

Atty. Ref.: 900-410

Filed: January 8, 2002

Group: 2825

For: METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE AND THE
SEMICONDUCTOR DEVICE MANUFACTURED BY THE METHOD

Examiner: Lee, Calvin

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May 7, 2004

Mail Stop: Issue Fee
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

COMMENTS ON STATEMENT OF REASONS FOR ALLOWANCE

The instant application was allowed February 18, 2004. However, the Reasons for Allowance are not commensurate with the scope of the claims.

For example, and without limitation, claim 13 does not require thermal treating for forming a second silicide film "on a substrate's surface" as recited in the reasons for allowance.

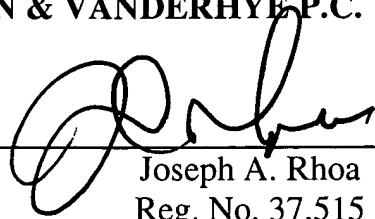
Please let me know if you should have any questions.

SOTOME, Yoshihiro
Serial No. **10/038,680**

Respectfully submitted,

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By:



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